

P-Channel Enhancement Mode Power MOSFET

Description

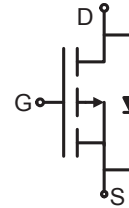
The RM2333 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

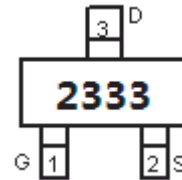
- $V_{DS} = -12V, I_D = -6A$
 $R_{DS(ON)} < 45m\Omega(max) @ V_{GS} = -2.5V$
 $R_{DS(ON)} < 30m\Omega(max) @ V_{GS} = -4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management
- Halogen-free
- P/N suffix V means AEC-Q101 qualified, e.g:RM2333V



Schematic diagram



Marking and pin assignment



SOT-23 top view

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2333	RM2333	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current -Continuous	I_D	-6	A
Drain Current -Pulsed ^(Note 1)	I_{DM}	-20	A
Maximum Power Dissipation	P_D	1.8	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	69	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-12	-	-	V

Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-12V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.65	-1.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-6A$	-	19	30	m Ω
		$V_{GS}=-2.5V, I_D=-5A$	-	26	45	
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-6A$		17	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=-6V, V_{GS}=0V,$ $F=1.0MHz$	-	1100	-	PF
Output Capacitance	C_{oss}		-	390	-	PF
Reverse Transfer Capacitance	C_{rss}		-	300	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-6V, I_D=-1A,$ $R_L=6\Omega, V_{GEN}=-4.5V, R_g=6\Omega$	-	25	-	nS
Turn-on Rise Time	t_r		-	45	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	72	-	nS
Turn-Off Fall Time	t_f		-	60	-	nS
Total Gate Charge	Q_g	$V_{DS}=-6V, I_D=-6A, V_{GS}=-4.5V$	-	11.5	-	nC
Gate-Source Charge	Q_{gs}		-	1.5	-	nC
Gate-Drain Charge	Q_{gd}		-	3.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-1.0A$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-6	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

RATING AND CHARACTERISTICS CURVES (RM2333)

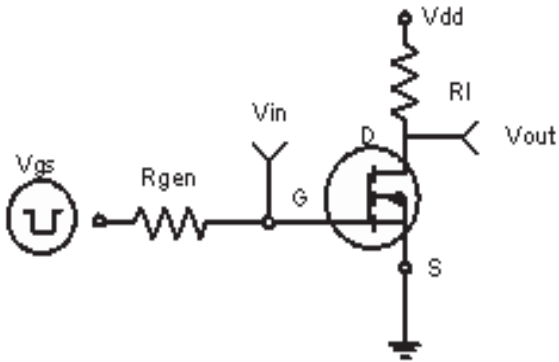


Figure 1: Switching Test Circuit

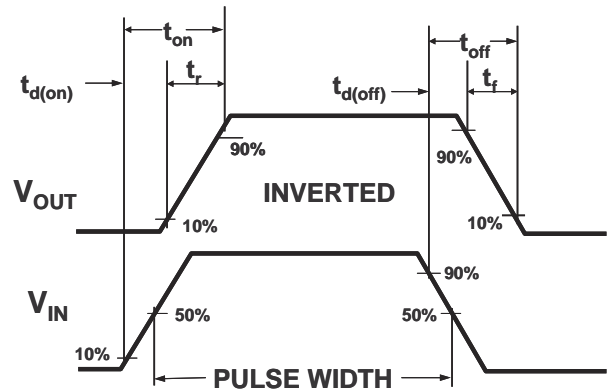
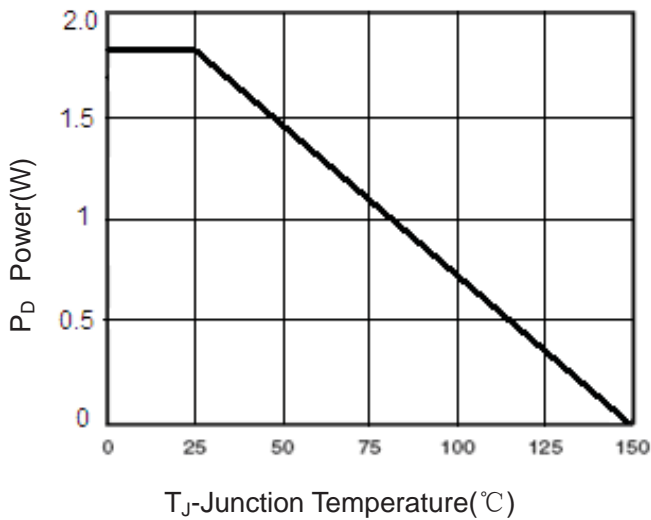
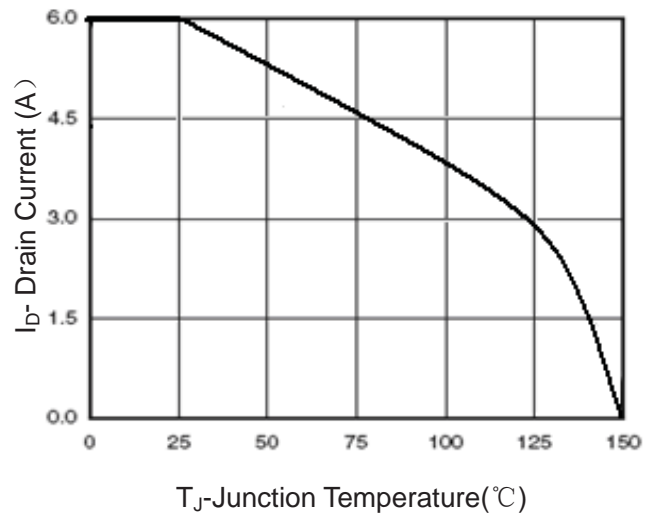


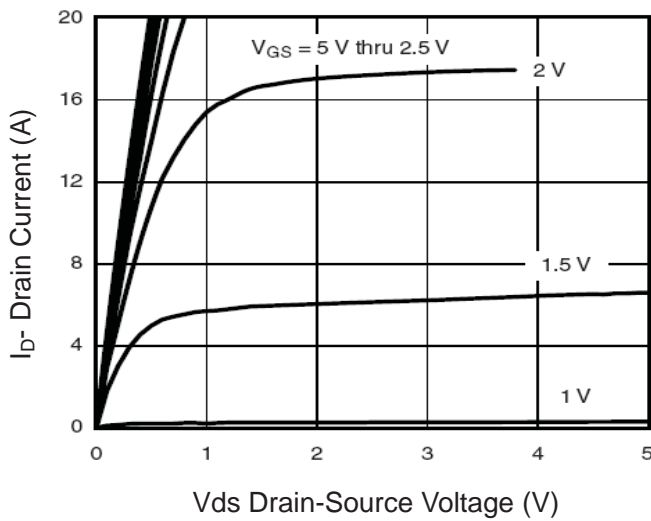
Figure 2: Switching Waveforms



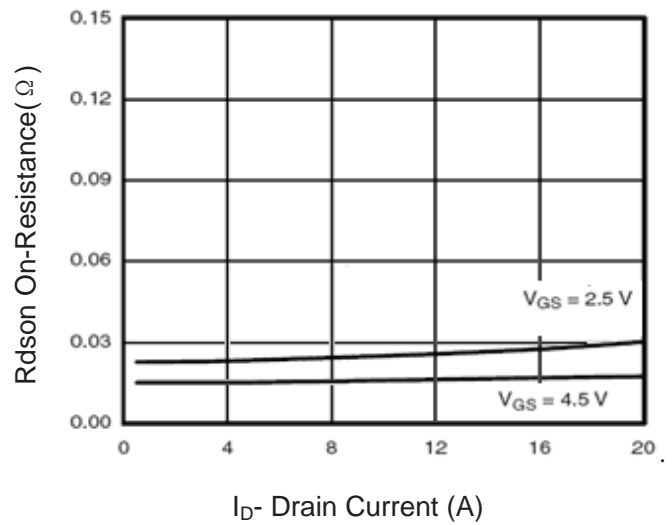
T_J-Junction Temperature (°C)
Figure 3 Power Dissipation



T_J-Junction Temperature (°C)
Figure 4 Drain Current

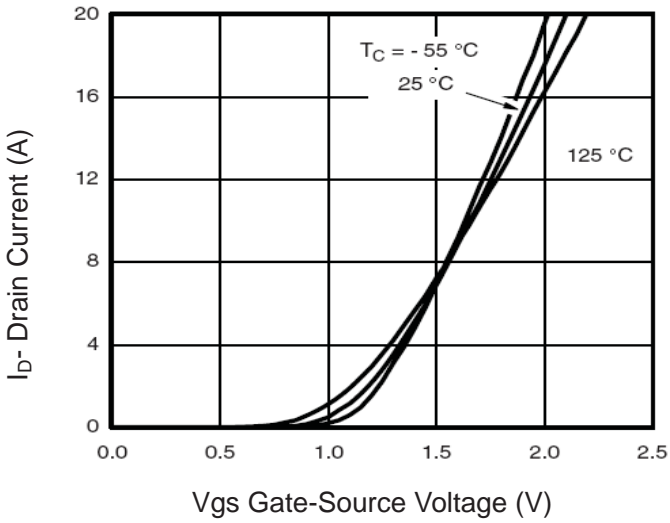


V_{ds} Drain-Source Voltage (V)
Figure 5 Output Characteristics

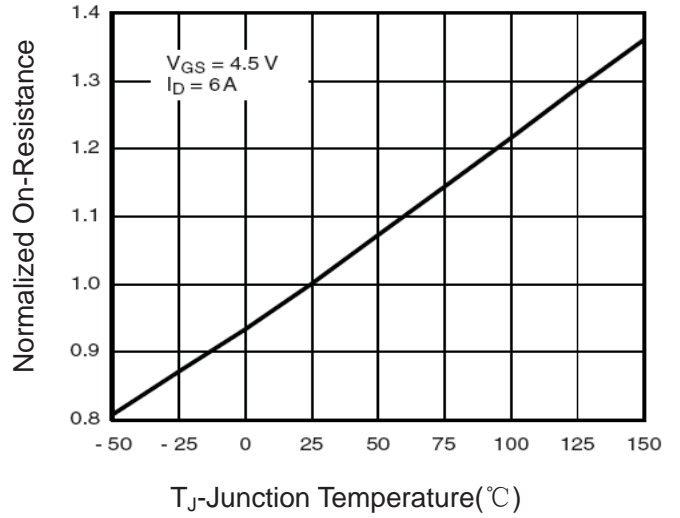


I_D-Drain Current (A)
Figure 6 Drain-Source On-Resistance

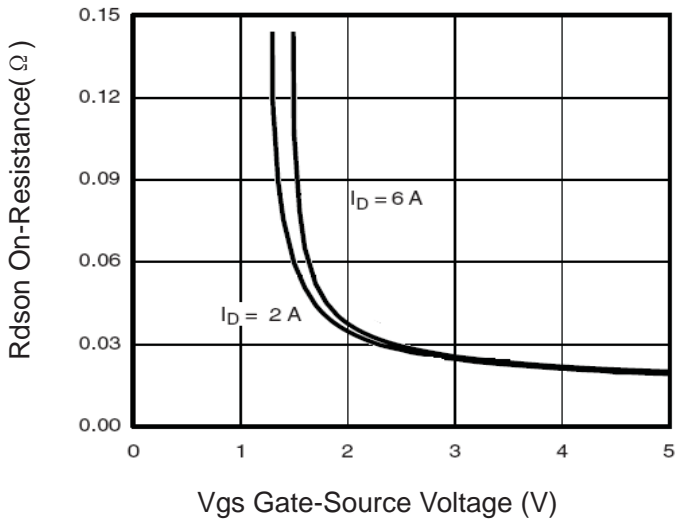
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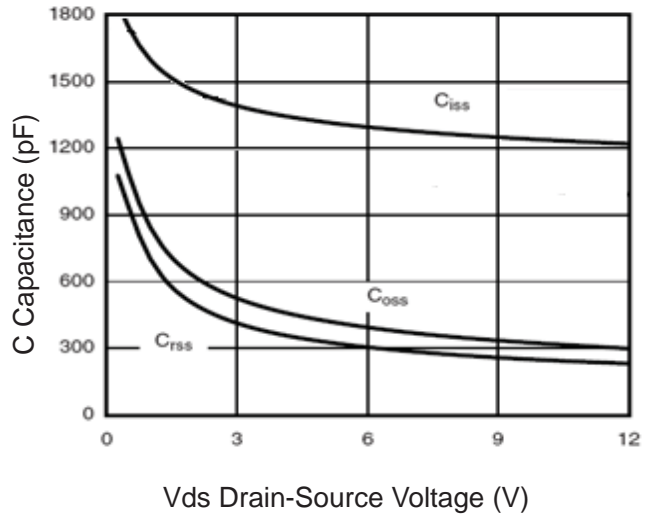
Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



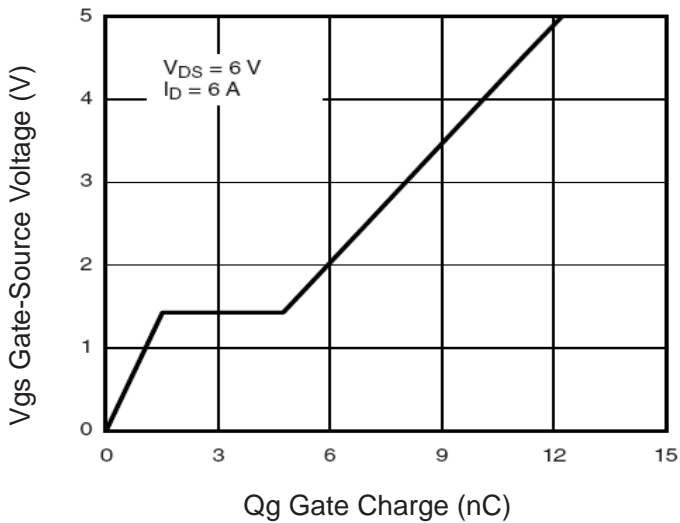
T_J -Junction Temperature($^\circ\text{C}$)
Figure 8 Drain-Source On-Resistance



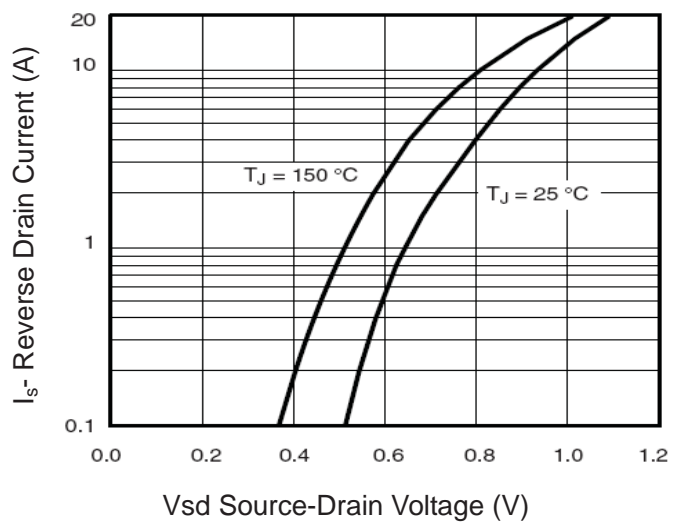
Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs



Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



Qg Gate Charge (nC)
Figure 11 Gate Charge



Vsd Source-Drain Voltage (V)
Figure 12 Source-Drain Diode Forward

RATING AND CHARACTERISTICS CURVES (RM2333)

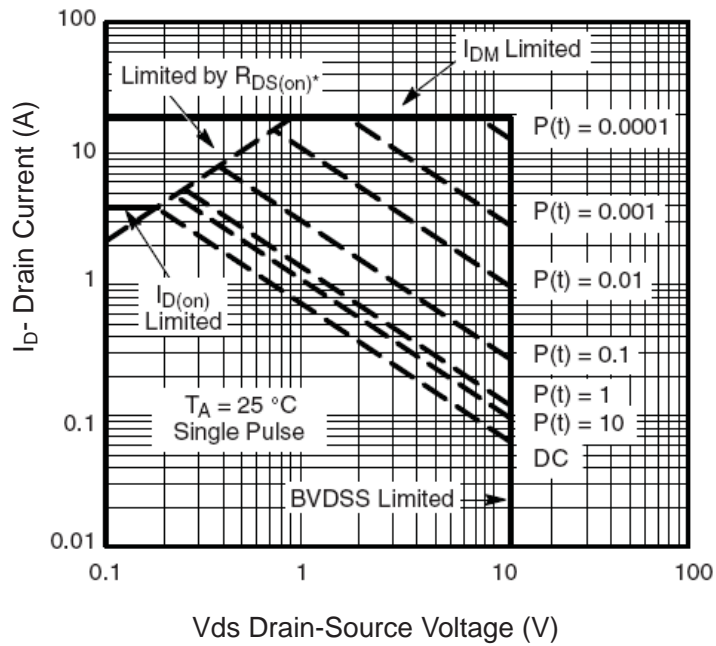


Figure 13 Safe Operation Area

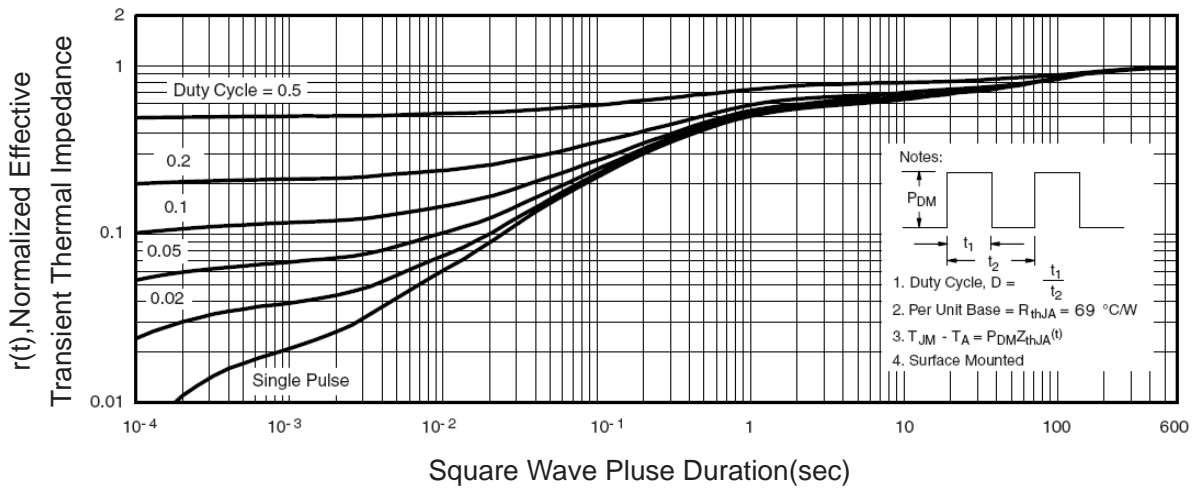
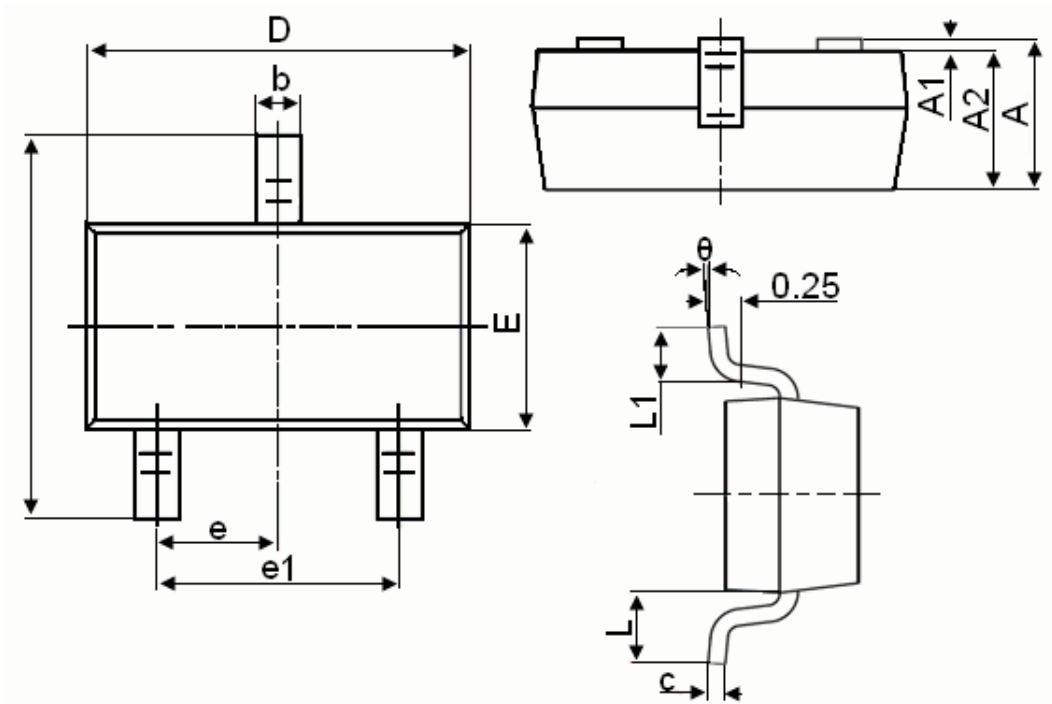


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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